



IGBT Discrete

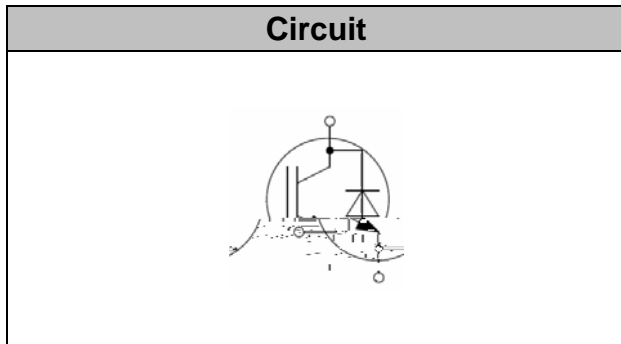
V_{CE}	650	V
I_C	75	A
$V_{CE(SAT)}$ $I_C=75A$	1.65	V

Applications

- .
- .
- .
- .

Features

- .
- .
- .
- .
- .



Maximum Ratings

Parameter	Symbol	Value	Unit



Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						



Electrical Characteristics of the Diode

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						

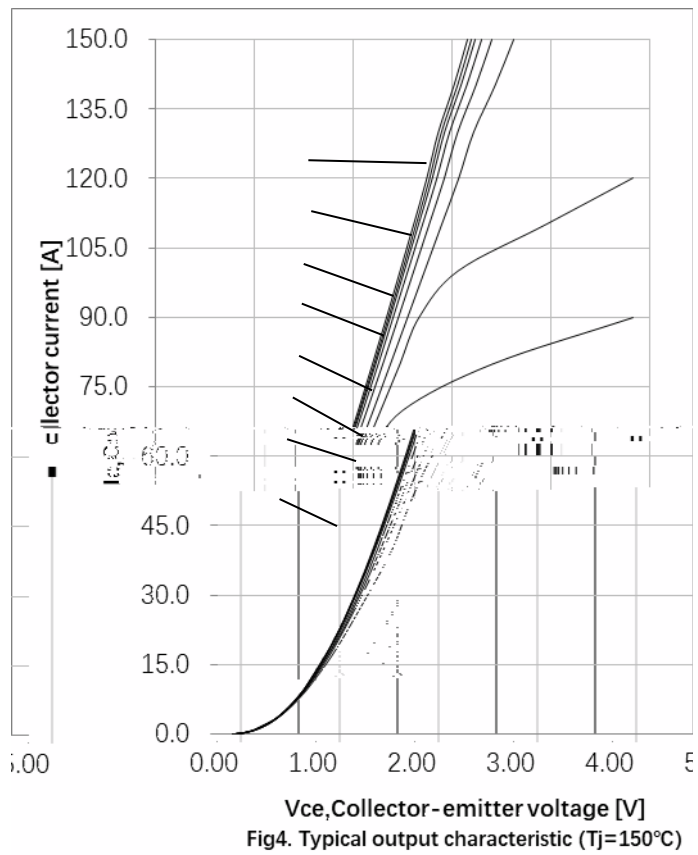
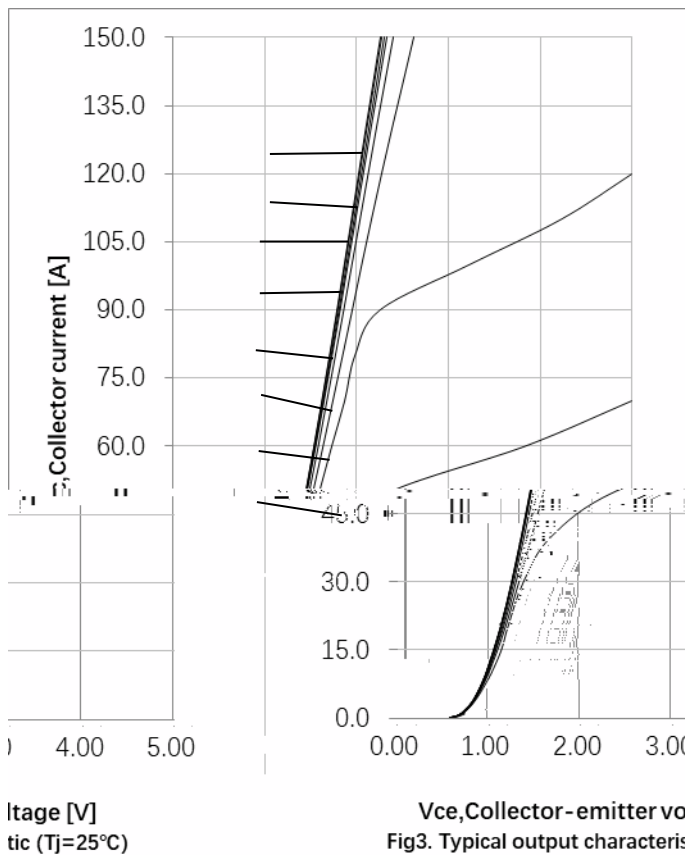
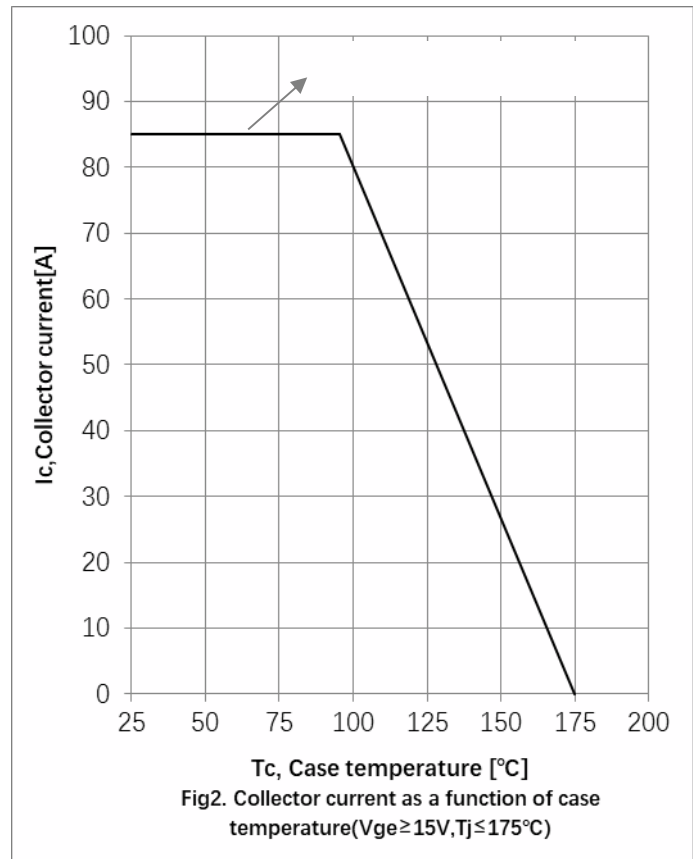
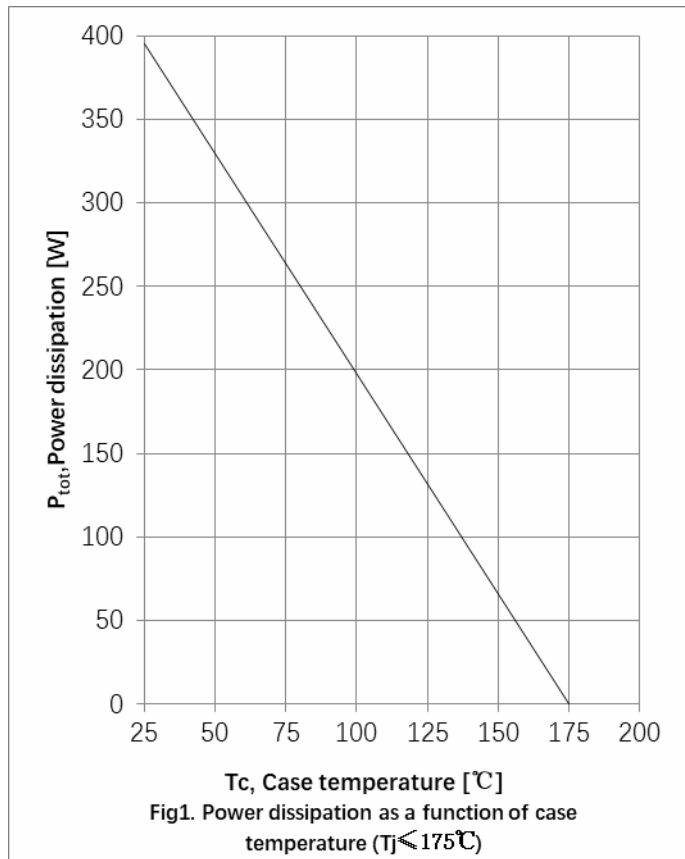
Thermal Resistance

Parameter	Symbol	Max. Value	Unit



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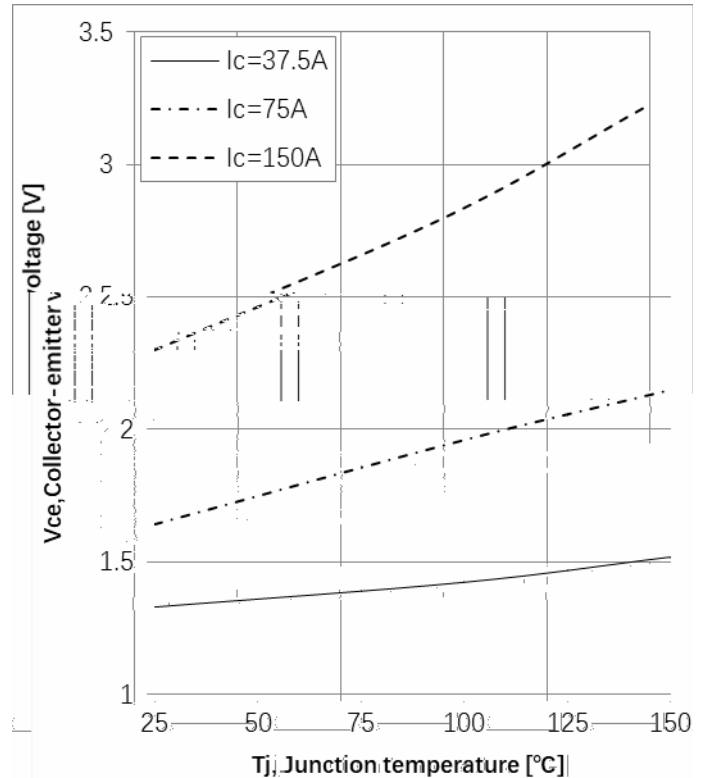


Fig6. Typical collector-emitter saturation voltage as a function of junction temperature (Vge=15V)

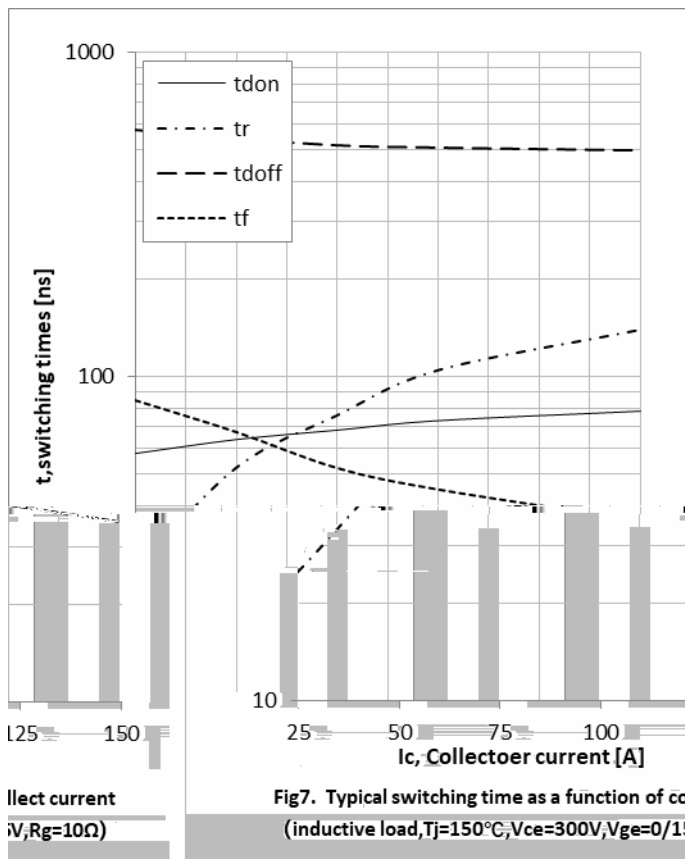


Fig7. Typical switching time as a function of collector current (inductive load, Tj=150°C, Vce=300V, Vge=0/15V, Rg=10Ω)

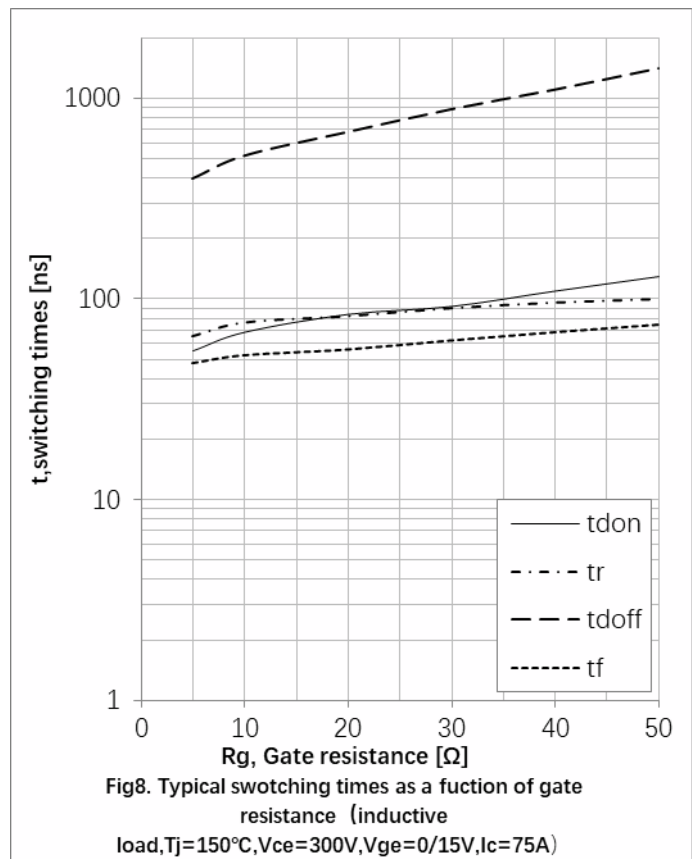
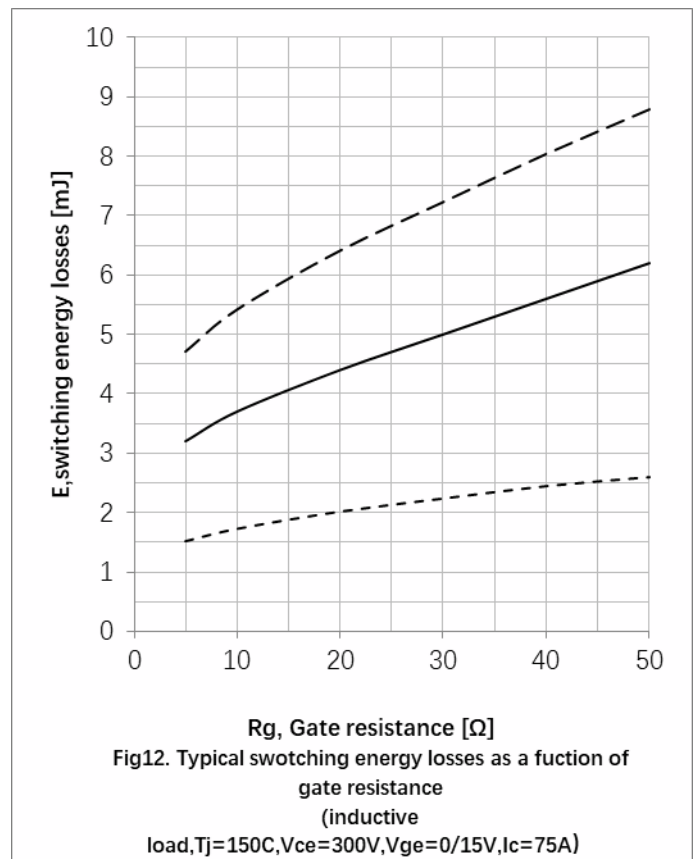
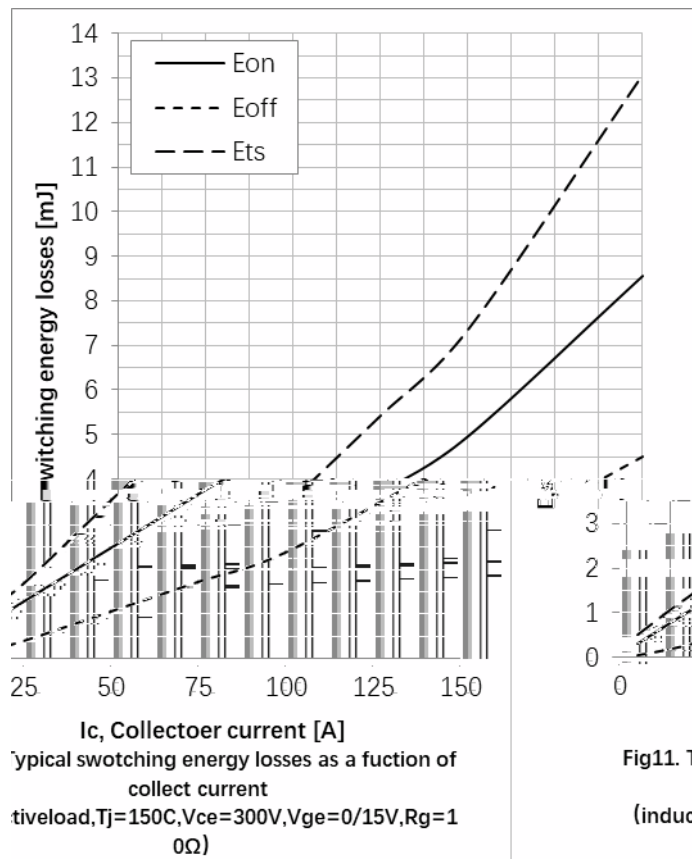
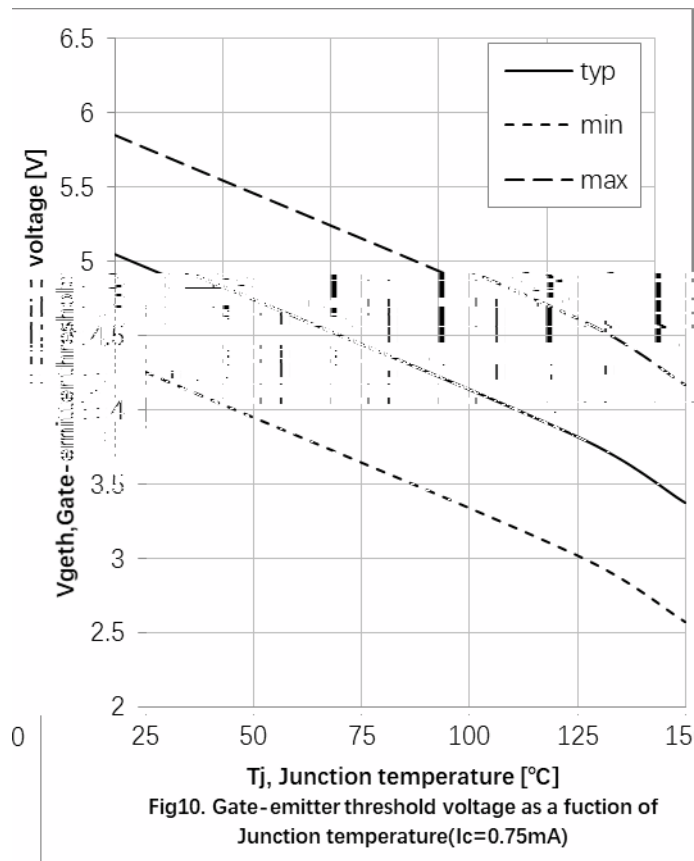
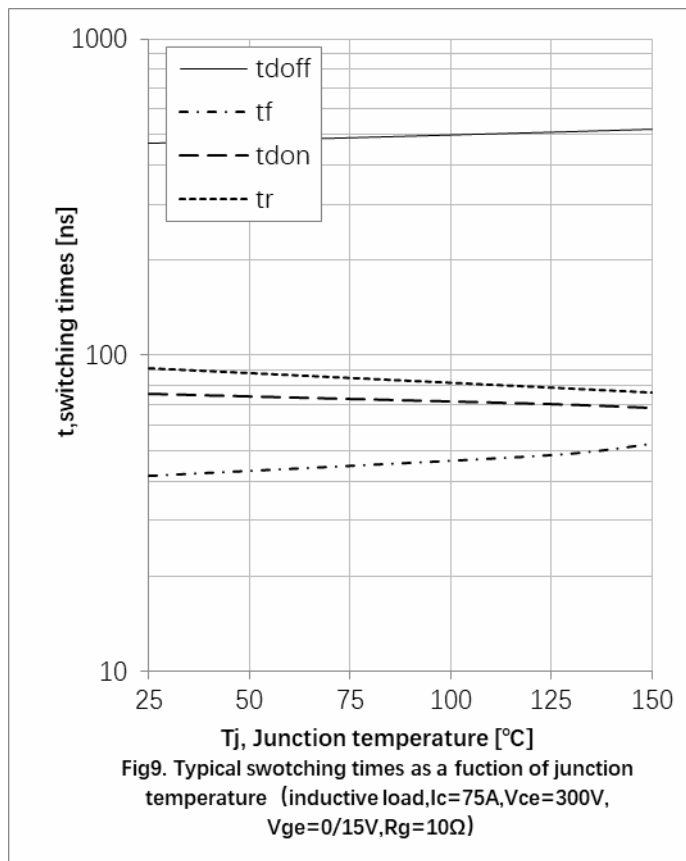


Fig8. Typical switching times as a function of gate resistance (inductive load, Tj=150°C, Vce=300V, Vge=0/15V, Ic=75A)



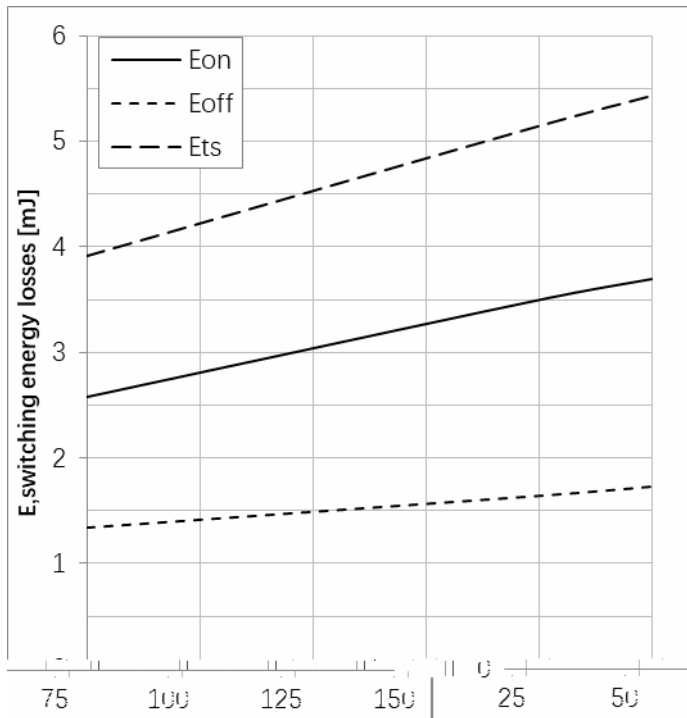


Fig13. Typical switching energy losses as a function of junction temperature [°C]

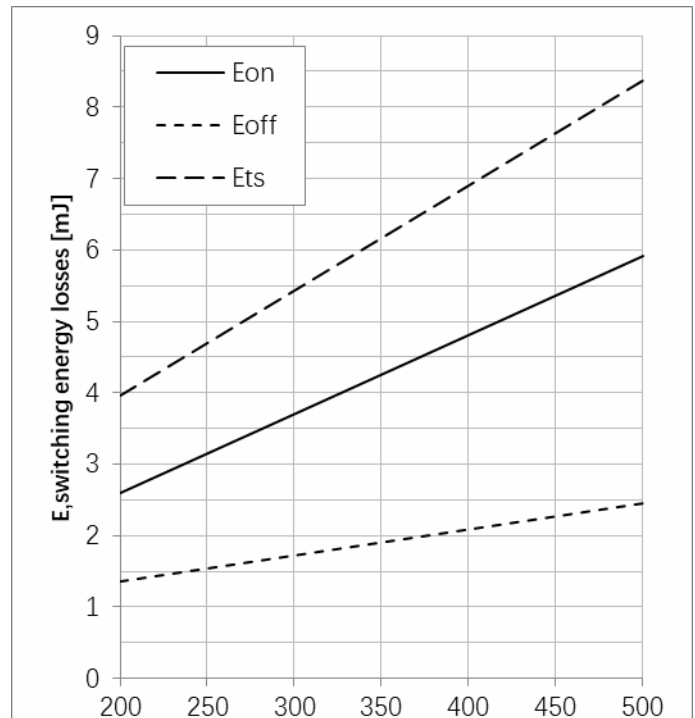


Fig14. Typical switching energy losses as a function of collector-emitter voltage (inductive load, $T_J=150^{\circ}\text{C}, I_c=75\text{A}, V_{ge}=0/15\text{V}, R_g=10\Omega$)

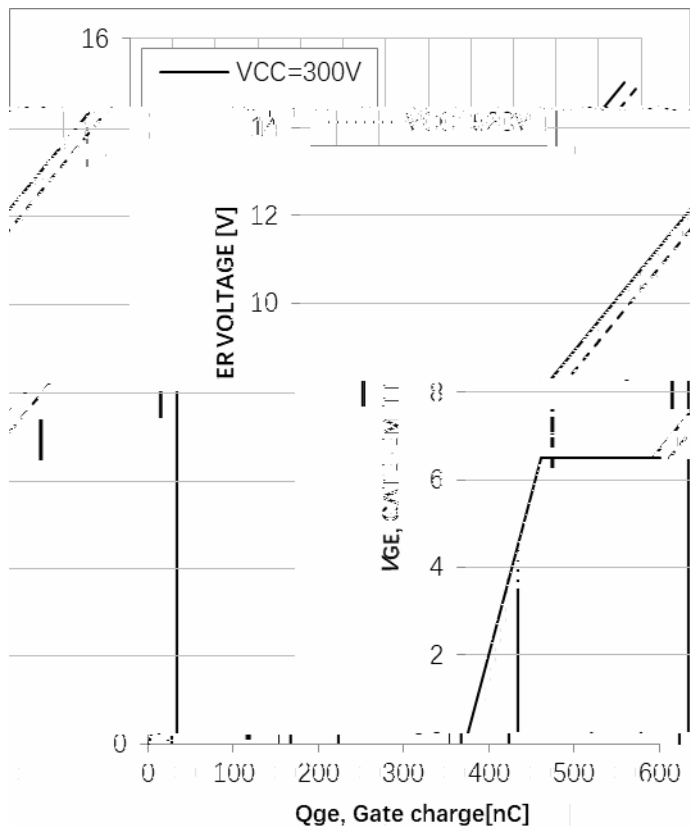


Fig15. Typical gate charge

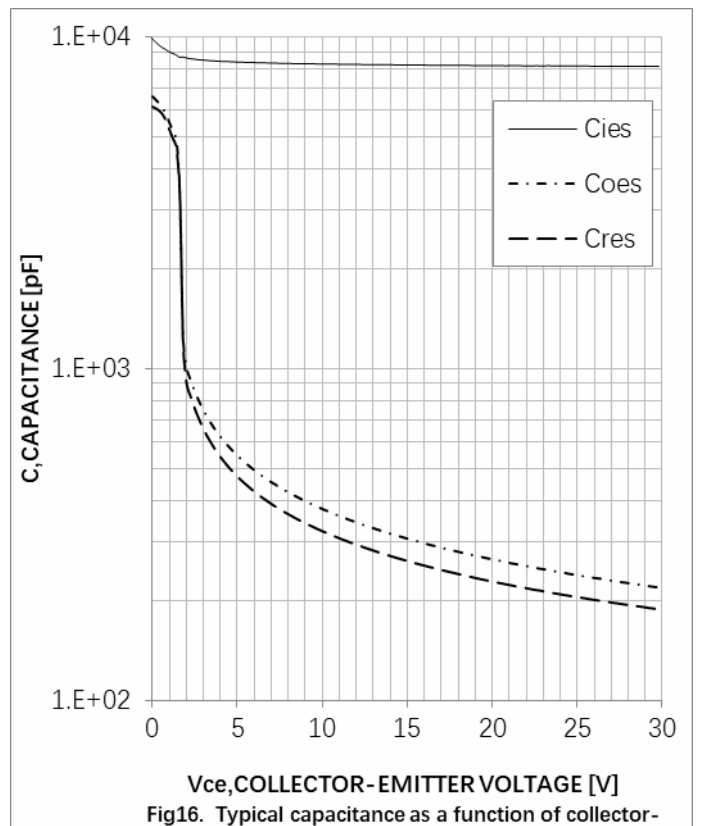
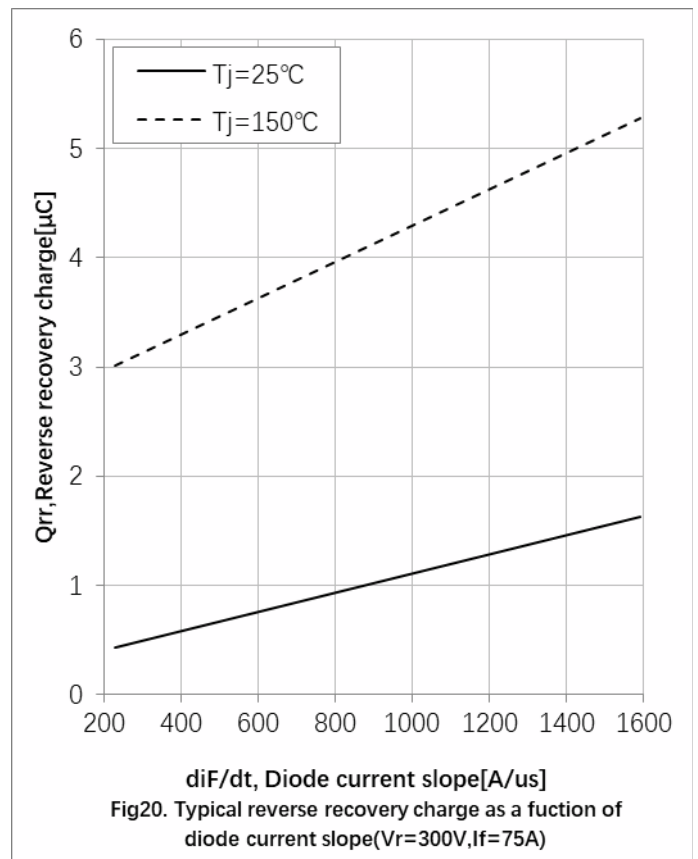
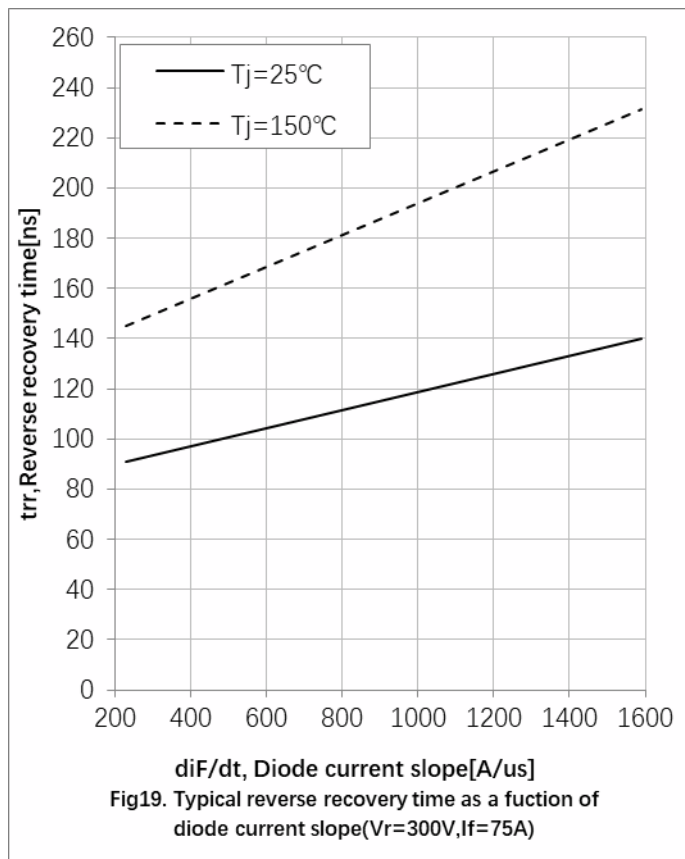
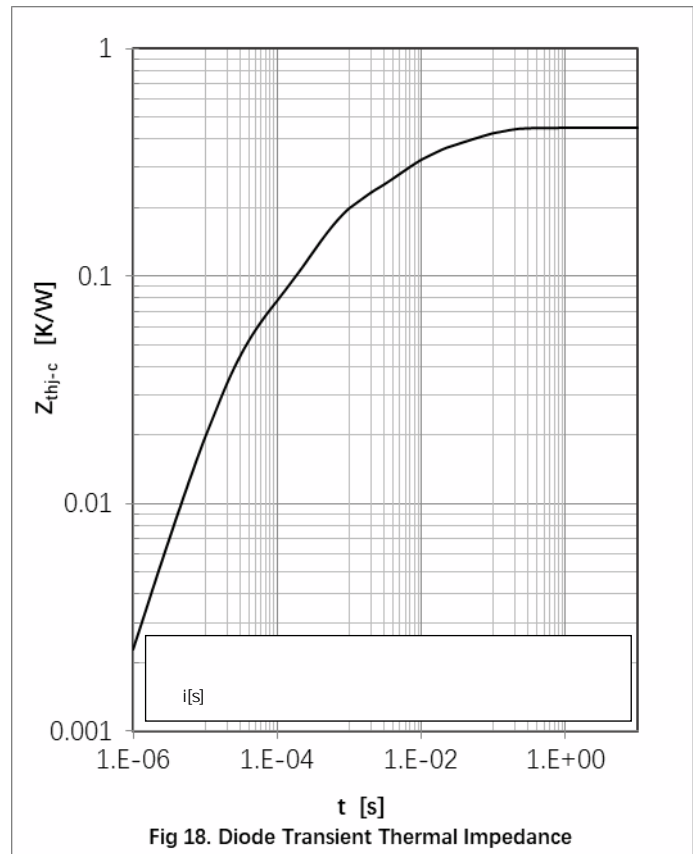
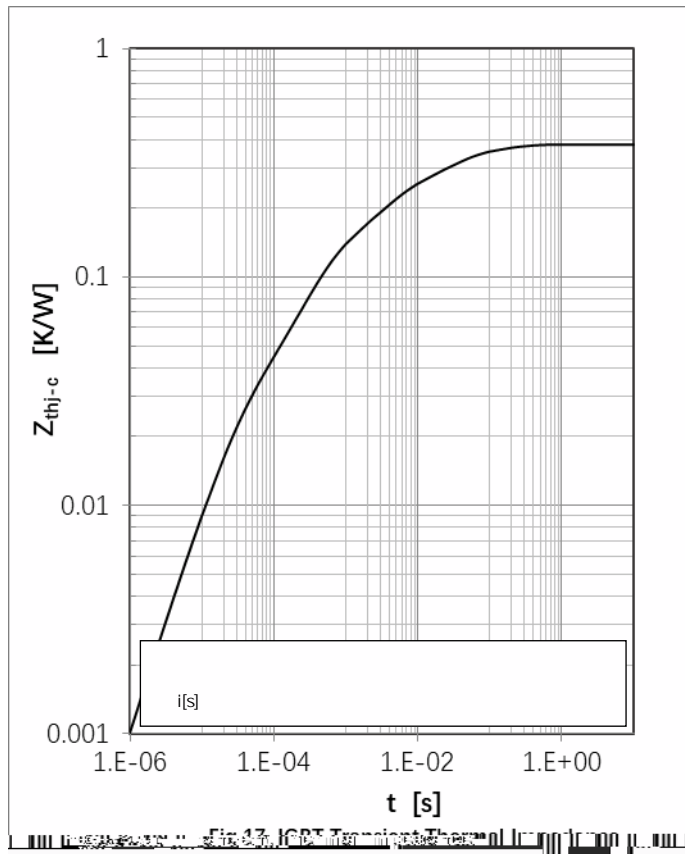


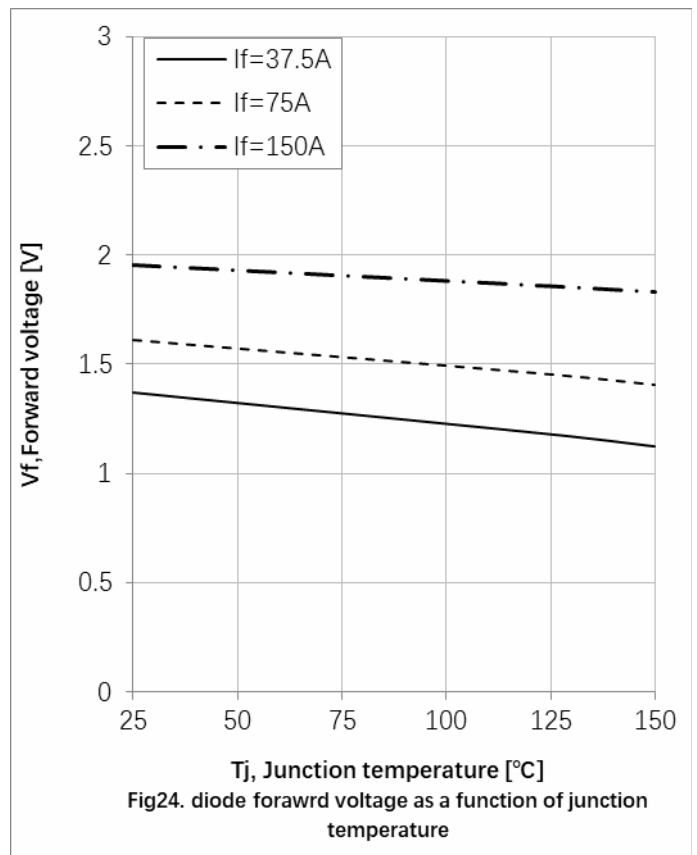
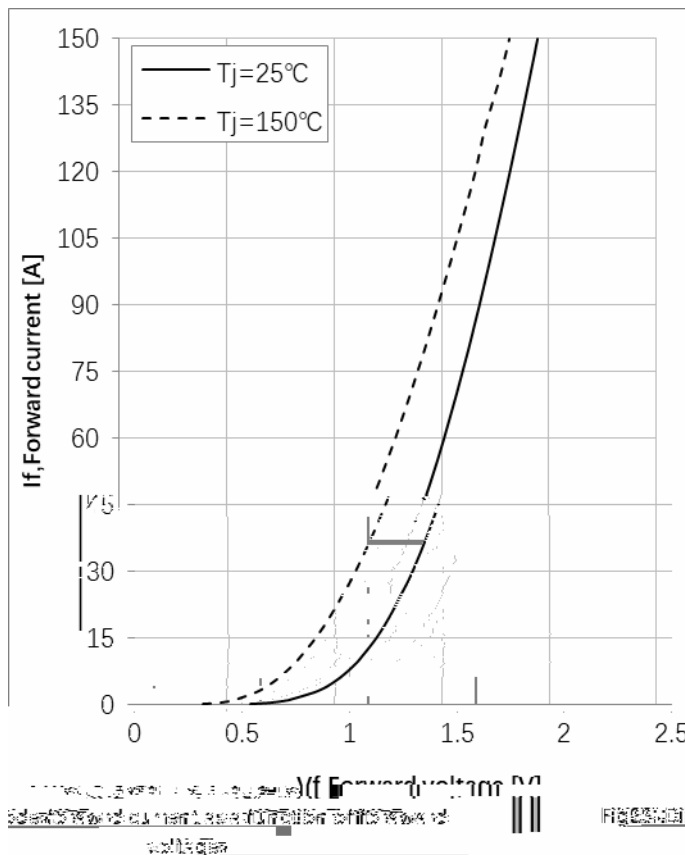
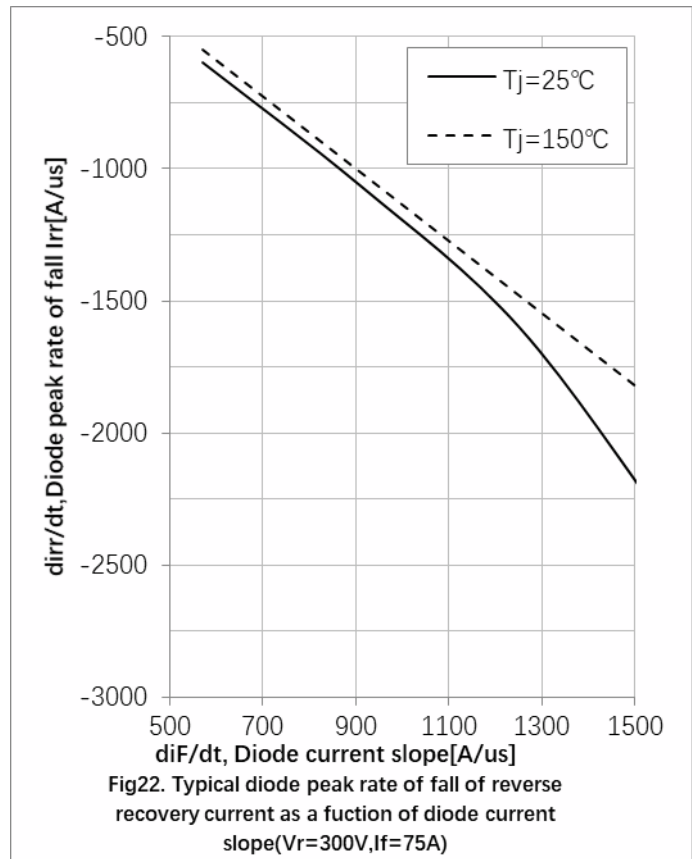
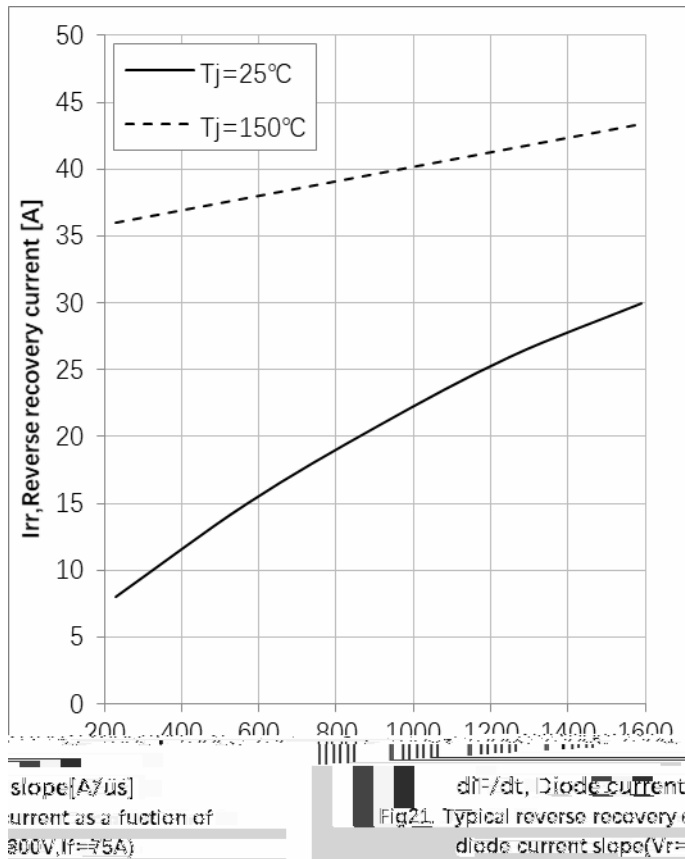
Fig16. Typical capacitance as a function of collector-emitter voltage



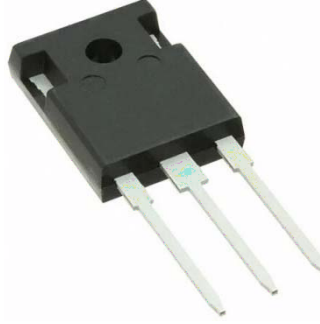
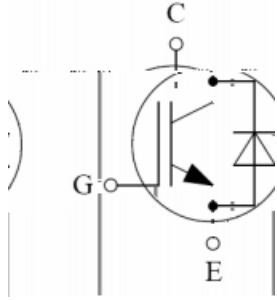


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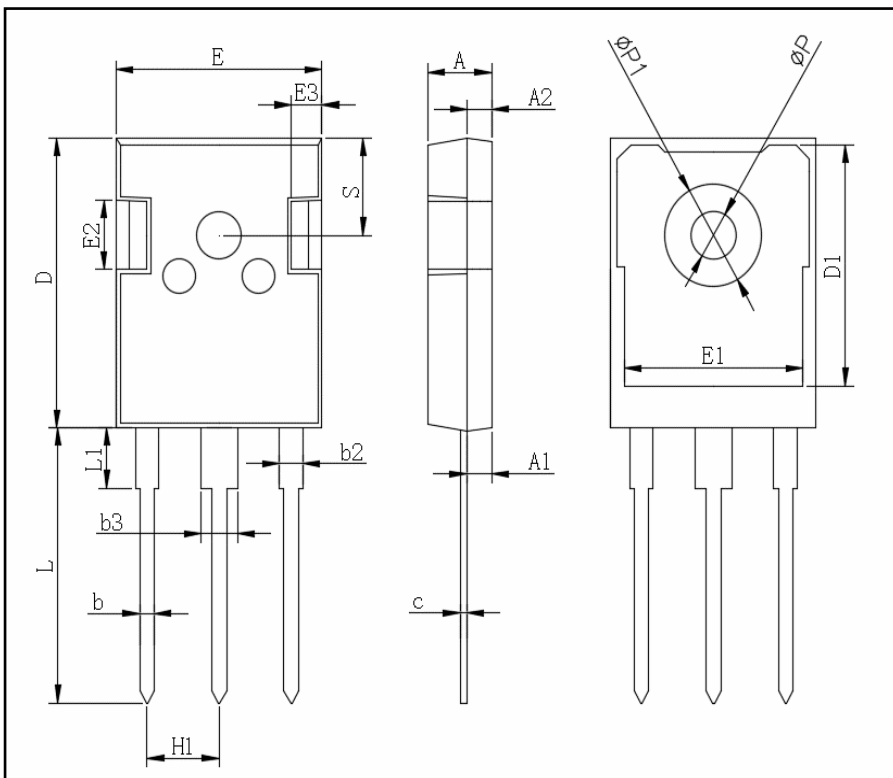
RoHS
COMPLIANT



Circuit Diagram



Package Outline Information



TO-247AB		